

# Towards High Contrast Potassium Double Tungstate Rib Waveguides For Laser Applications



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## Objective

The main objective of the **RENOS project** (Rare Earth doped Novel On-chip Sources) is to develop very compact, power efficient, tunable lasers that operate in a wide frequency range.

These lasers will be beneficial in applications in optical sensing, spectroscopy, metrology and telecommunications.

## Material

The devices will be made from **rare-earth doped potassium double tungstate** (RE:KY(WO<sub>4</sub>)<sub>2</sub> or KYW) because it possesses:

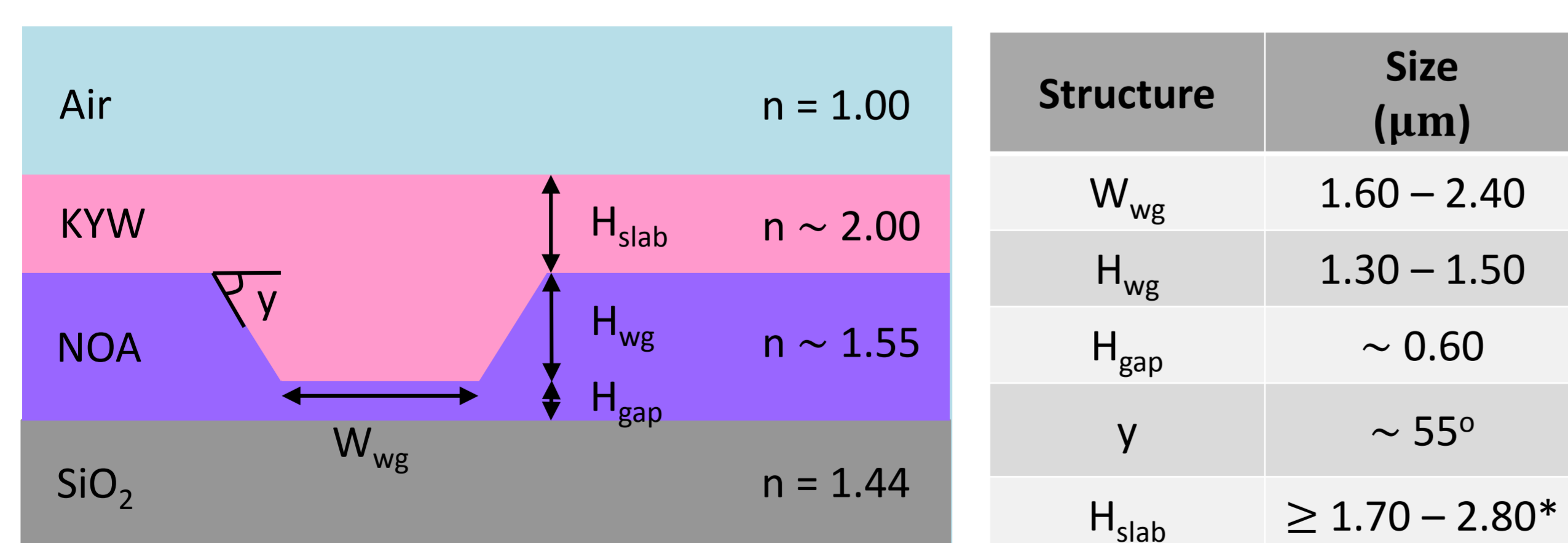
- High refractive index ( $n \sim 2.00$  @ 1550 nm)
- High allowed dopant concentration
- High emission and absorption cross-section for rare-earth ions

Those characteristics will make it possible to obtain:

- Highly confined waveguides
- Ring resonators with large FSR
- Ring resonators with high Q-factor
- Efficient four-wave mixing and Raman scattering

## Simulation

Numerical analyses for single mode condition of the high-contrast waveguides are performed using the software Lumerical MODE. The calculated optimal parameters for the structure shown in the figure are listed in the table.

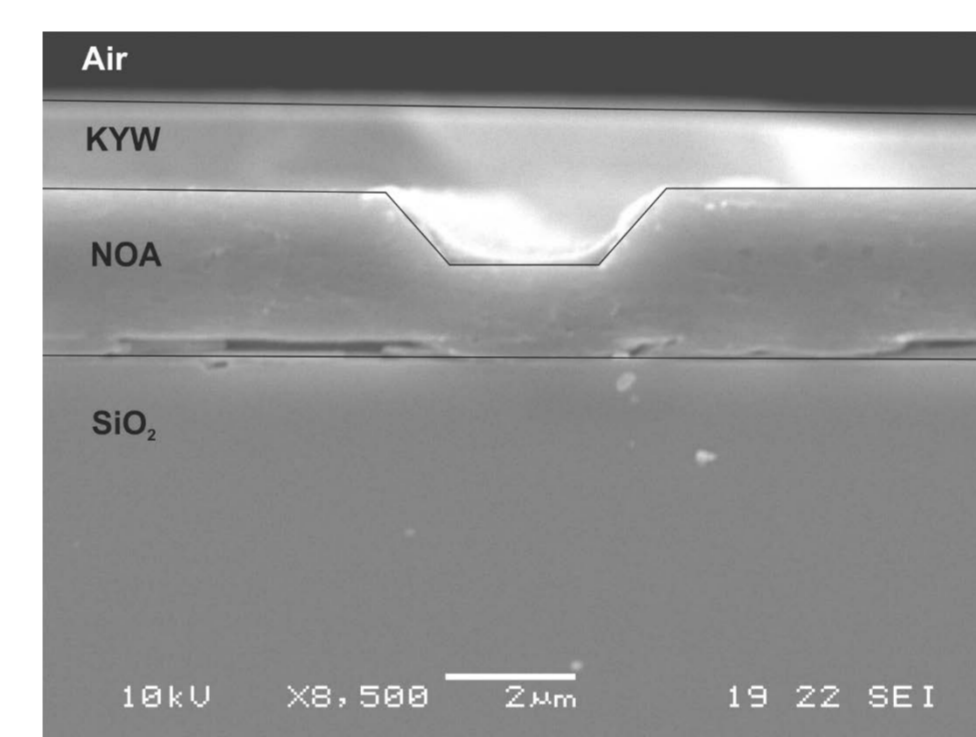


\*Limit for single mode conditions for smallest and largest rib configuration

## Fabrication

Fabrication flow:

- 1) The patterned sample is flip-chip bonded onto a SiO<sub>2</sub> carrier with Norland Optical Adhesive NOA 81.
- 2) The sample is mounted with wax on a thick glass plate.
- 3) Coarse lapping with 9 μm Al<sub>2</sub>O<sub>3</sub> particles on an iron disk (Logitech LP50), lapping speed 4-5 μm/min, to a total height of 50 μm.
- 4) Fine lapping with 1 μm Al<sub>2</sub>O<sub>3</sub> particles on an iron disk, lapping speed 1-2 μm/min to a total height of 7 μm.
- 5) Polishing with 40 nm SiO<sub>2</sub> particles on a polyurethane disk, polishing speed ~1 μm/hour to desired height (or until polishing stop).



20% Er:KYW single mode waveguides. Fabricated with technology proposed by M.A. Sefüncü [1] (fabrication flow without 4<sup>th</sup> step). Structure dimensions,  $W_{wg} = 2.3$  μm,  $H_{wg} = 1.1$  μm,  $H_{gap} = 1.5$  μm,  $H_{slab} = 1.5$  μm,  $\gamma = 54^\circ$ .

## Polishing stop

A **polishing stop** has been designed and fabricated in order to improve thickness control. The polishing stop is created by etching a 12x12 mm<sup>2</sup> pool in the SiO<sub>2</sub>. The KYW sample (10x10 mm<sup>2</sup>) is bonded inside it before lapping. Upon reaching the pool edge, the increase in surface area slows down the polishing to 10-30%.



Schematic representation of the KYW substrate with waveguides after polishing.

Challenges:

- Fabrication tolerance of:
  - SiO<sub>2</sub> pool < 100 nm
  - $H_{wg}$  of KYW < 100 nm
- Well defined glue thickness